## Spin injection into a short DNA chain

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Quantum spin transport through a short DNA chain connected to ferrom agnetic electrodes has been investigated by the transferm atrix m ethod. W e describe the system by a tight-binding m odel where the parameters are extracted from the experimental data and realistic metal energy bands. For ferrom agnetic iron electrodes, the magnetoresistance of a 30-basepair Poly (G)-Poly (C) DNA is found to be lower than 10% at a bias of < 4 V, but can reach up to 20% at a bias of 5 V. In the presence of the spin- ip mechanism, the magnetoresistance is signi cantly enhanced when the spin-ip coupling is weak but as the coupling becomes stronger the decreasing magnetoresistance develops an oscillatory behavior.

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In recent years, a rem arkable progress in direct m easurements of electron transport through DNA has generated intense interest in DNA electronics [1, 2, 3, 4, 5, 6, 7, 8, 9, 10, 11, 12, 13]. DNA is found to have diverse electronic properties depending on its structure and the environment around it [6]. The clear sem iconductor behavior observed in a short DNA chain of 30basepair Poly (G) - Poly (C) has been explained by a tightbinding m odel [2, 9, 11]. On the other hand, spin transport through nanostructures has, of late, been receiving considerable attention because of the possiblity of developing spin-based electronic devices [14]. Inspired by the broad interest in spin-injection into mesoscopic systems

[15], we have investigated the quantum spin transport [10] through a short DNA chain connected to ferrom agnetic electrodes. We predict an enhancement and oscillation of magnetoresistance in this system taking into account the realistic band structure of ferrom agnetic Fe electrode and a spin-ip mechanism .

We consider a p-type sem iconductor DNA chain of N basepairs connected to a circuit via m etalelectrodes. The tight-binding Ham iltonian of the system is

$$H = H_d + H_L + H_R + H_{dm} + H_{dps} + H_{sp}$$
 (1)

where

$$H_{d} = X^{N} \qquad X^{N} \qquad X^{N-1} \qquad T_{d} (C_{n}^{y}, C_{n+1}; + C_{n+1}^{y}, C_{n}; );$$

$$H_{L} = X^{n-1} \qquad X^{n-$$

Here  $C_n^{y}$ , is the creation operator of electron with spin on site  $n \in 1;$ trode (n 0), and the right electrode (n N + 1).H<sub>d</sub> describes electrons (holes) of spin in the DNA chain with the on-site energies  $"_{d}$  ("\_{d}), which is equal to the highest occupied m olecular orbit (HOMO) energy of each

base-pair, and the hopping param eters  $t_d$  between neigh-;N) of the DNA chain, the left elec-boring sites. The HOMO energy band is then determ ined by ", and t, . The Fermi energy  $E_F$  in the p-type DNA chain locates between the HOMO and lowest unoccupied molecular orbit (LUM 0) bands and is closer to the HOMO band edge. Experim ental results have indicated

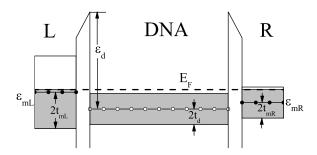


FIG.1: Energy band of the system in equilibrium .

that the Ferm i energy m ay vary from sample to sample [2].  $H_X$  with X = L or R denotes the Ham iltonian of electrons in the left electrode (L) or the right electrode (R). In the tight-binding model, " $_{\rm m\,X}$  is the center of the energy band where the electrons are in the metals and 4t<sub>mx</sub> its band width. W hen the DNA chain contacts to the metal electrodes, exchange of electrons (holes) between the DNA chain and the electrodes becom es possible. In equilibrium, as illustrated in Fig. 1, the Ferm i energies of the electrodes and of the DNA match and a tunnelling barrier form s between them . The contact property is described by the tunnelling parameter  $t_{\rm dm}$  . W hen a bias voltage drop is applied over the electrodes, distribution of the voltage drop or the potential pro le along the non-equilibrium system depends on the DNA chain property and its contact with the metal electrodes. Since the free electron density in the metals is much higher than that in DNA, we assume that the band structure of the m etal electrode is not changed by the applied bias. When the contact between DNA and the electrodes is poor, the voltage drop concentrates on the contact. In case of a perfect contact how ever, the whole voltage drop should be applied mainly along the DNA chain. In this letter, we assume the voltage drop is on the contact since it is supported by the t to the experim ental result (see below).

In realworld, a DNA chain is composed of two strands of bases with one phosphate-sugar backbone connected to each strand. The backbones can a ect the on-site energy of electrons in the basepairs. Further, the environm ent around the DNA chain m ay also play a role in the property of the electrons. Here we use a reservoir of sem i-in nite chain [9, 16, 17] with a energy band of width 4 and a coupling of strength to each DNA basepair site to m im ic the e ect of the backbones and the environm ent. As a result, the on-site energy of each site in the DNA basepair is modiled by a self energy \_ n (E) which is energy dependent and is expressed as,

$$_{n}(E) = \frac{2}{E \quad "r \quad r}$$

with "r being the on-site energy of the sem i-in nite reservoir chain which we assume to be equal to the DNA onsite energy and r = (E "r)=2 i[<sup>2</sup> (E "r)<sup>2</sup>=4]<sup>1=2</sup> the self energy of any reservoir site which is obtained self-consistently. In what follows, we have used the values = 0:1 eV and = 5 eV [9]. To study the spin relaxation for a possible spin injection, we introduce the term H<sub>sp</sub> in the H am iltonian to take into account the spin ip on-site and between neighboring sites described by the parameters  $t_d^{so}$  and  $t_d^s$  respectively. The spin- ip along the DNA can be a result of spin-orbit interaction, m agnetic in purity in the backbone, orm agnetic environment.

In order to evaluate the transport properties of the system, we have employed the transferm atrix m ethod [4, 5]. For an open system, the secular equation of the system is expressed as a group of in nite number of equations of the form,

The wave functions of sites n + 1 and n are related to those of sites n and n = 1 by a transfer m atrix  $\hat{M}$ ,

with

and  $n_{n+1} = (t_{n+1})^2 (t_{n+1}^s)^2$ . A sum ing plane wave functions for the electrons  $n = (A e^{ik_L na} + A)^2$ 

B e  $^{ik_{L}na}$ ) for n 0 and  $_{n} = ^{r}$  C e $^{ik_{L}na}$  for n N + 1 in the left and right electrodes respectively, we can express the output wave am plitude C in terms of the

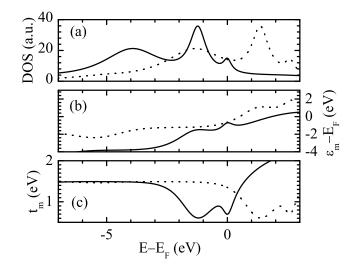


FIG. 2: Energy dependence of the parameters  $"_m$  (b) and  $t_m$  (c) for ferrom agnetic Fe. Solid curves and dotted curves correspond to spin-up and spin-down electrons. The resulting bulk DOS is also shown in (a).

input wave amplitude A and the transm ission,

$$T (E) = \frac{jC f \sin(k_R a)}{jA^+ f \sin(k_L^+ a) + jA f \sin(k_L a)};$$

We  $a_{\rm q}$  <u>choose a</u> normalized incident amplitude A = 1= jsin ( $k_{\rm L}$  a) j. The net current primarily comes from transmission of electrons of energy between the electrodes' Ferm i energies and is calculated as [17]

$$I = \frac{e^2 X}{h} \int_{-1}^{X} dE T (E) [f_L (E) f_R (E)]$$

with the Ferm i function f (E) =  $1 = \exp [(E \quad E_F) = k_B T]$ and the room temperature T = 300 K. For ferrom agnetic electrodes the m egnetoresistance is de ned as the percentage change of resistance between parallel and antiparallel con gurations  $R_m = (R_{anti} \quad R_{paral}) = R_{anti} = (I_{paral} \quad I_{anti}) = I_{paral}$ .

In metals, an electron of energy E may come from di erent energy bands. The corresponding e ective param eters  $"_{m X}$  and  $t_{m X}$  are then an average of the param eters of these bands and are energy dependent. In linear or quasi-equilibrium system, they are approximately the values near the Ferm i energy. In a non-equilibrium system, if the di erence of the Ferm i levels between the two electrodes is comparable to the energy band width of the metals, the energy dependence should be taken into account. In the existing experiments the applied bias can be higher than 4 eV, which is larger than the width of the d bands where the Ferm i level locates in many metals. In the case of Ferrom agnetic Fe which exemplies the electrode material here, approximately ve bands can be identied from the density of states (DOS)

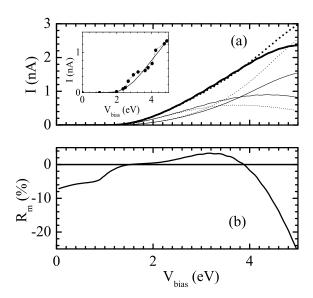


FIG.3: (a) The I-V curve of a 30-basepair Poly (G) Poly (C) DNA between two ferrom agnetic Fe electrodes of parallel (solid curves) and anti-parallel (dotted) con gurations. The thicker curves illustrate the total currents and the thinner ones the contribution from the two spin branches. (b) The m agnetoresistance vesus the applied bias potential. In the inset of (a), we show our theoretical t (thick solid curve) to the experim ental result ( lled circles connected by dotted lines) in Ref. [2].

near the Ferm i energy of the bulk m aterial [18]. For the spin-up (m a jority) electrons, the ve bands locate approximately at 2.5, 0, 0.68, 3.4, and 7 eV above the Ferm i energy with band width 6, 0.3, 0.6, 4.1, and 3.7 eV respectively. For the spin-down (m inority) electrons, the energy bands are the same as above but shifted 2.58 eV to higher energy. U sing Lorentzian broadening, we can m in ic the bulk DOS and extract the parameters "m and tm as shown in Fig. 2. At the Ferm i energy, we get the hopping parameters 0.39 eV and 1.62 eV for spin-up and spin-down electrons respectively which coincide with the result obtained from the Ferm i velocity [10].

Just as in Ref. [9], we extract the parameters of the DNA chain by tting the experimental result of Ref. [2]. By evaluating the energy-dependent parameters " $_{\rm m}$  and t $_{\rm m}$  from Platinum's band structure [19], we can t the experimental result as shown in the inset of Fig. 3 (a). As a result, we nd that the hopping parameter is t $_{\rm d}$  = 0.6 eV, the equilibrium Ferm i energy is 1.73 eV higher than the DNA HOMO on-site energy, the contact parameters are t $_{\rm dm}$  = 0.019 eV for the right electrode and 0.013 eV for the left, 1/3 of the bias voltage drop at the right contact and 2/3 at the left. The above parameters are close to those obtained in Ref. [9] except for a larger t $_{\rm dm}$  in the present case.

For ferrom agnetic Fe electrodes as shown in Fig. 3(a), we get two I-V curves corresponding to the parallel (solid curves) and antiparallel (dotted curves) m agnetization

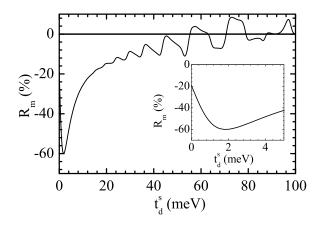


FIG. 4: The magnetoresistance vesus the spin- ip parameter  $t_d^s$  in DNA when a bias of 4.8 eV is applied. The other parameters are the same as in Fig. 3.

con gurations for the left and right electrodes, using the same contact parameter  $t_{dm} = 0.02$  eV for the two electrodes. In Fig. 3(b), the magnetoresistance which describe the percentage change of the resistance of the system when being switched from parallel to antiparallel con guration, is plotted. In contrast to the results where constant values of the parameters "m and tm at the Ferm i energy were used, here we nd a much smaller magnetoresistance until a strong bias is applied. This can be understood from the energy dependence of tm shown in Fig. 2(c). Instead of two parallel lines at 1.4 eV and 0.6 eV, the curves of tm Ferm i energy. This crossing makes the magnetoresistance disappear around the bias volt-

age  $V_{\text{bias}} = 2 \text{ eV}$ . The increase of magnetoresistance at higher bias voltage results from the increasing  $t_m$  spread between spin-up and spin-down electrons in the range of 2 eV around the Fermi energy.

In Fig. 4, we show how a spin-ip mechanism can a ect the spin injection, assuming that the spin-ip can happen only when an electron jump from one site to another. The magnetoresistance does not decay monotonically to zero. Instead, the magnetoresistance is enhanced when there is a very weak spin-ip coupling ( $t_a^s < 1.9 \text{ m eV}$ ) as a result of the quantum interference in the system. In the transm ission spectrum, peaks are slightly split with the increase of  $t_a^s$ , indicating the mixing of the spin-up and spin-down states in the system due to the spin- ip coupling. W e observe an increase in magnetoresistance from 20% at  $t_d^s = 0$  to 60% at  $t_d^s = 1.9$  m eV as displayed in the inset of Fig. 4. Then the magnetoresistance decreases sm oothly until  $t_d^s = 20 \text{ meV}$  . Above that value, the magnetoresitance begins to oscillate when it decays to zero.

In sum m ary, we have investigated the quantum spin transport through a short DNA chain connected to ferrom agnetic electrodes. We have used a tight-binding m odel to describe the system where the parameters are extracted from the experimental results and realistic energy bands of m etals. We nd that the energy band structure of the ferrom agnetic electrodes signi cantly a ects the resulting spin transport. In the presence of the spin- ip m echanism, enhancement and oscillation of m agnetoresistance due to m ixing of spin states are also observed.

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